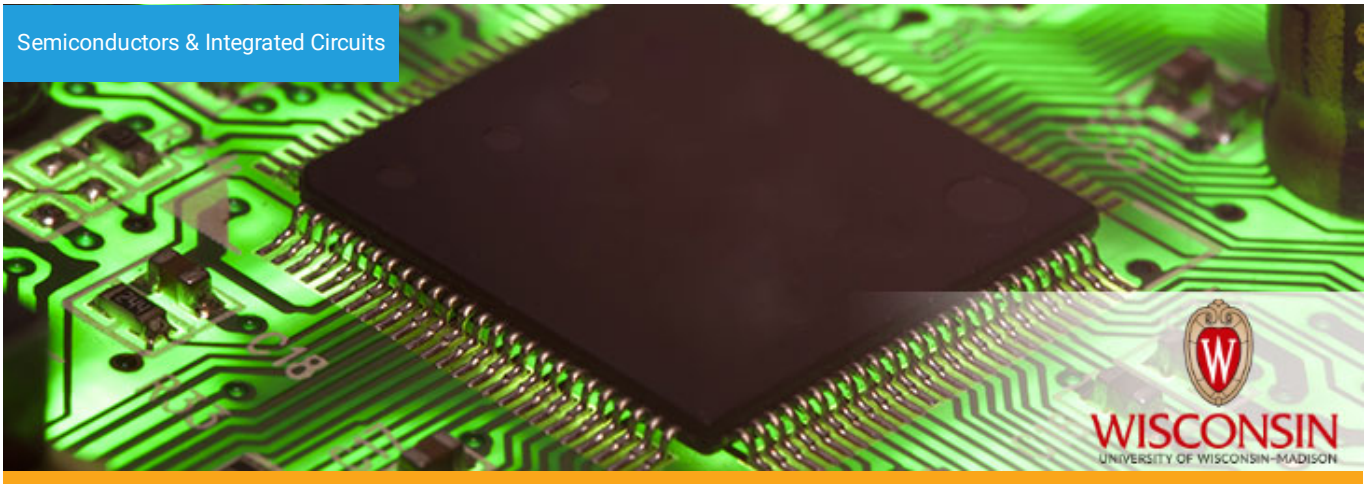




METAL ORGANIC CHEMICAL VAPOR DEPOSITION OF SEMI-INSULATING EXTRINSICALLY CARBON-DOPED GROUP III-NITRIDE FILMS

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Overview

III-nitride materials, such as AlN, GaN, InN, and their solid solutions, possess properties that are simply not accessible in any other semiconductors. However, there are unique processing challenges related to the crystal structure and bonding.

The Invention

UW-Madison Researchers have developed semi-insulating, extrinsically carbon-doped group III-nitrides, such as gallium nitride, and methods for growing extrinsically carbon-doped group III-nitrides, such as gallium nitride, on a substrate via MOCVD.

Tech Fields

- [Semiconductors & Integrated Circuits : Components & materials](#)

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